

UTF3055

Power MOSFET

N-CHANNEL ENHANCEMENT
MODE POWER MOSFET

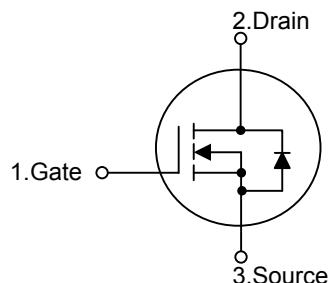
■ DESCRIPTION

As an N-channel enhancement mode power MOSFET, the UTC **UTF3055** is designed for low voltage, high speed switching applications in power supplies, converters and power motor controls and bridge circuits.

■ FEATURES

* $R_{DS(ON)} < 110 \text{ m}\Omega$ @ $V_{GS} = 10V$

■ SYMBOL



■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
-	UTF3055G-AA3-R	SOT-223	G	D	S	Tape Reel
UTF3055L-TN3-R	UTF3055G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: S: Source G: Gate D: Drain

UTF3055G-AA3-R 	(1) R: Tape Reel (2) AA3: SOT-223, TN3: TO-252 (3) G: Halogen Free and Lead Free, L:Lead Free
--------------------	---

■ MARKING

SOT-223	TO-252
 Data Code 1	 Lot Code 1 Data Code G: Halogen Free L: Lead Free

■ ABSOLUTE MAXIMUM RATINGS ($T_c = 25^\circ\text{C}$, unless otherwise noted)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain Source Voltage		V_{DSS}	60	V
Drain Gate Voltage ($R_{GS} = 10\text{M}\Omega$)		V_{DGR}	60	V
Gate Source Voltage	Continuous	V_{GSS}	± 20	V
	Non-Repetitive ($t_P \leq 10 \text{ ms}$)		± 30	V
Continuous Drain Current ($T_a = 25^\circ\text{C}$)		I_D	3.0	A
Pulsed Drain Current ($t_P \leq 10 \mu\text{s}$)		I_{DM}	9.0	A
Single Pulsed Avalanche Energy (Note 2)		EAS	74	mJ
Power Dissipation ($T_a = 25^\circ\text{C}$) (Note 3)	SOT-223	P_D	0.83	W
	TO-252		1.136	
Derate above 25°C	SOT-223		14	mW/ $^\circ\text{C}$
	TO-252		20	
Junction Temperature		T_J	175	$^\circ\text{C}$
Strong Temperature		T_{STG}	-55 ~ +175	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. $T_J = 25^\circ\text{C}$, $V_{DD} = 25\text{V}$, $V_{GS} = 10\text{V}$, $I_L = 7.0\text{A}$, $L = 3.0\text{mH}$, $V_{DS} = 60\text{V}$

3. When surface mounted to an FR4 board using 1" pad size, 1 oz. (Cu. Area 1.127 sq in).

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient (Note)	SOT-223	θ_{JA}	150	$^\circ\text{C/W}$
	TO-252		110	$^\circ\text{C/W}$

Note: When surface mounted to an FR4 board using 1" pad size, 1 oz. (Cu. Area 1.127 sq in).

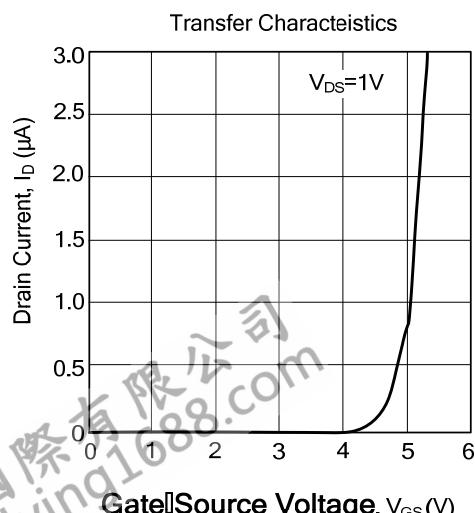
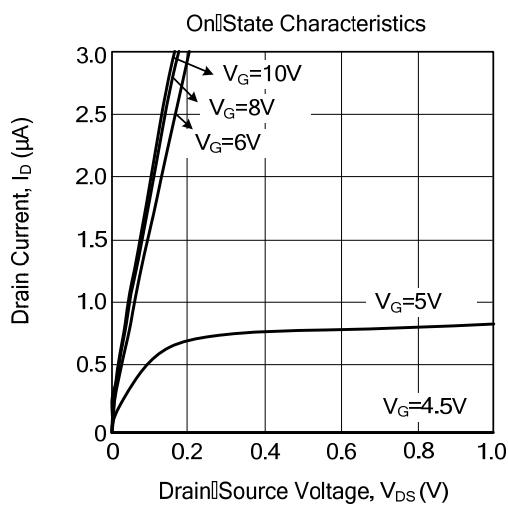
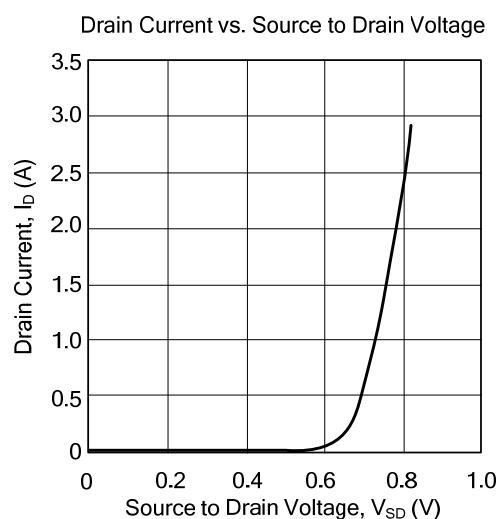
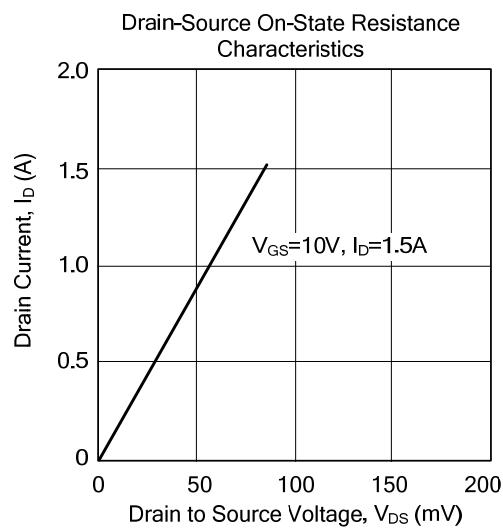
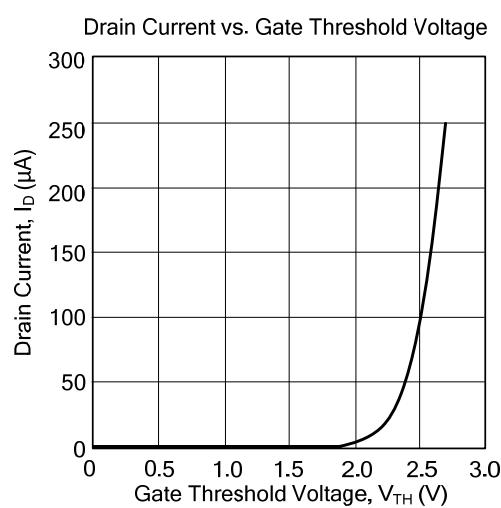
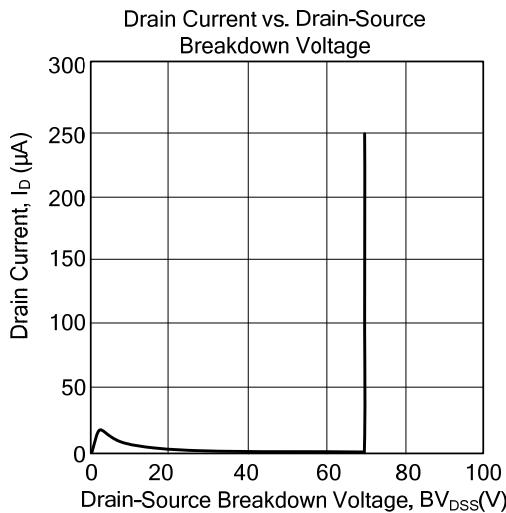
■ ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain Source Breakdown Voltage (Note 1)	BV_{DSS}	$V_{\text{GS}} = 0\text{V}, I_{\text{D}} = 250\mu\text{A}$	60	68		V
Temperature Coefficient (Positive)				66		mV°C
Drain-Source Leakage Current	I_{DSS}	$V_{\text{GS}} = 0\text{V}, V_{\text{DS}} = 60\text{V}$		1.0		μA
Gate-Source Leakage Current	I_{GSS}	$V_{\text{GS}} = \pm 20\text{ V}, V_{\text{DS}} = 0\text{V}$			± 100	nA
ON CHARACTERISTICS (Note 1)						
Gate Threshold Voltage	$V_{\text{GS(TH)}}$	$V_{\text{GS}} = V_{\text{DS}}, I_{\text{D}} = 250\mu\text{A}$	2.0	3.0	4.0	V
Temperature Coefficient (Negative)				6.6		mV°C
Static Drain-Source On-State Resistance	$R_{\text{DS(ON)}}$	$V_{\text{GS}} = 10\text{ V}, I_{\text{D}} = 1.5\text{A}$		88	110	$\text{m}\Omega$
Static Drain-to-Source On-Resistance	$V_{\text{DS(ON)}}$	$V_{\text{GS}} = 10\text{ V}, I_{\text{D}} = 3\text{A}$		0.27	0.40	V
Forward Tran conductance	g_{FS}	$V_{\text{DS}} = 8.0\text{V}, I_{\text{D}} = 1.7\text{A}$		3.2		M
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{\text{GS}} = 0\text{ V}, V_{\text{DS}} = 25\text{ V}, f = 1.0\text{MHz}$		324	455	pF
Output Capacitance	C_{OSS}			35	50	pF
Reverse Transfer Capacitance	C_{RSS}			110	155	pF
SWITCHING PARAMETERS (Note 2)						
Turn-ON Delay Time	$t_{\text{D(ON)}}$	$V_{\text{GS}} = 10\text{V}, V_{\text{DD}} = 30\text{V}, I_{\text{D}} = 3.0\text{A}, R_{\text{G}} = 9.1\Omega$ (Note 1)		9.4	20	ns
Turn-ON Rise Time	t_{R}			14	30	ns
Turn-OFF Delay Time	$t_{\text{D(OFF)}}$			21	45	ns
Turn-OFF Fall-Time	t_{F}			13	30	ns
Total Gate Charge	Q_{G}	$V_{\text{GS}} = 10\text{V}, V_{\text{DS}} = 48\text{V}, I_{\text{D}} = 3.0\text{A}$ (Note 1)		10.6	22	nC
Gate-Source Charge	Q_{GS}			1.9		nC
Gate-Drain Charge	Q_{GD}			4.2		nC
Diode Forward Voltage	V_{SD}	$V_{\text{GS}} = 0\text{V}, I_{\text{S}} = 3.0\text{A}$		0.89	1.0	V
Body Diode Reverse Recovery Time	t_{RR}	$V_{\text{GS}} = 0\text{V}, I_{\text{S}} = 3.0\text{A}, \frac{dI}{dt} = 100\text{ A}/\mu\text{s}$ (Note 1)		30		ns
	t_{A}			22		ns
	t_{B}			8.6		ns
Body Diode Reverse Recovery Charge	Q_{RR}			0.04		nC

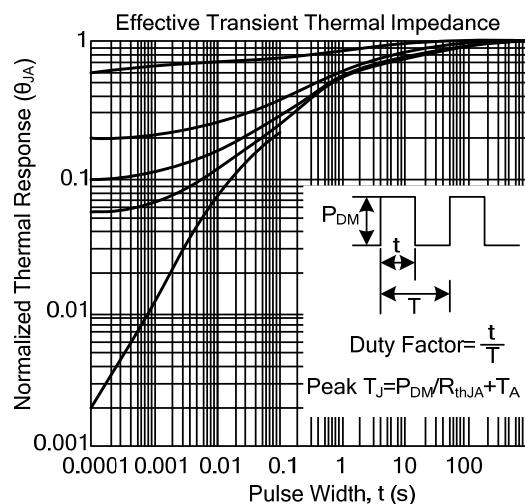
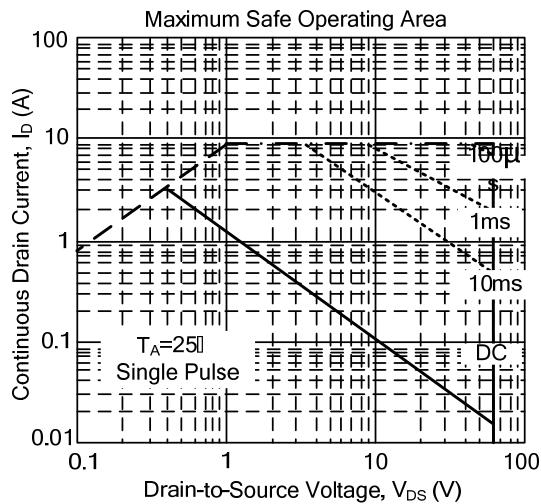
Notes: 1. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Switching characteristics are independent of operating junction temperatures.

■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.